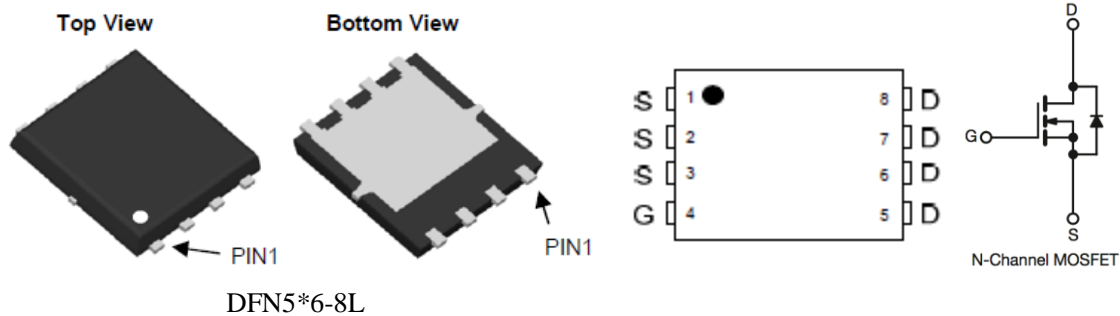


N-Channel Enhancement Mode Power MOSFET
● Features
 $V_{DS} = 100V,$
 $I_D = 83A$
 $R_{DS(ON)} @ V_{GS} = 10V, TYP 4.3m\Omega$
 $R_{DS(ON)} @ V_{GS} = 6.0V, TYP 5.2m\Omega$
 $R_{DS(ON)} @ V_{GS} = 4.5V, TYP 6.8m\Omega$
● General Description

- Notebook AC-in load switch
- Battery protection charge/discharge

● Pin Configurations

● Absolute Maximum Ratings @ $T_A=25^\circ C$ unless otherwise noted

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current (Continuous) *AC	$T_C=25^\circ C$	I_D	83	A
	$T_C=70^\circ C$		66.1	
Drain Current (Pulse) *B		I_{DM}	200	A
Power Dissipation	$T_C=25^\circ C$	P_D	83	W
Operating Temperature/ Storage Temperature		T_J/T_{STG}	-55~150	$^\circ C$

● Thermal Resistance Ratings

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient	$t \leq 10 s$	R_{thJA}	18	23	$^\circ C/W$
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1	1.5	

● Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise noted

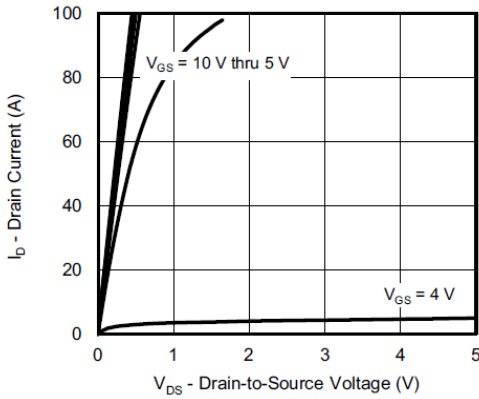
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$	--	--	1	μA
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_{DS} = 250\mu A$	1	2.1	3	V
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	--	--	± 100	nA
Drain-Source On-state Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$	--	4.3	5.5	m Ω
	$R_{DS(on)}$	$V_{GS} = 6.0V, I_D = 20A$	--	5.2	6.7	m Ω
	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 20A$	--	6.8	8.7	m Ω
Diode Forward Voltage	V_{SD}	$I_{SD} = 1A, V_{GS} = 0V$	--	0.69	1.2	V
Diode Forward Current *AC	I_S	$T_C = 25^\circ\text{C}$	--	--	83	A
Switching						
Total Gate Charge	Q_g	$V_{DS} = 50V, V_{GS} = 10V, I_D = 20A$	--	59	--	nC
Gate-Source Charge	Q_{gs}		--	10	--	nC
Gate-Drain Charge	Q_{gd}		--	13.5	--	nC
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 50V, V_{GEN} = 10V,$ $R_G = 4.5\Omega, R_L = 2.5\Omega,$ $I_{DS} = 20A$	--	13.2	--	ns
Turn-on Rise Time	t_r		--	40	--	ns
Turn-off Delay Time	$t_{d(off)}$		--	38	--	ns
Turn-Off Fall Time	t_f		--	66	--	ns
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 25V, V_{DS} = 10V, f = 1\text{MHz}$	--	3460	--	pF
Output Capacitance	C_{oss}		--	1940	--	pF
Reverse Transfer Capacitance	C_{rss}		--	194	--	pF

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

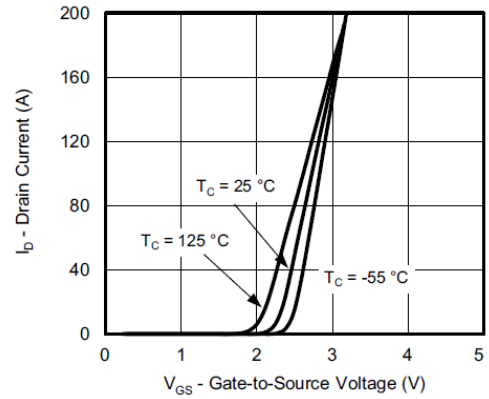
B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the $t \leq 10s$ junction to ambient thermal resistance rating.

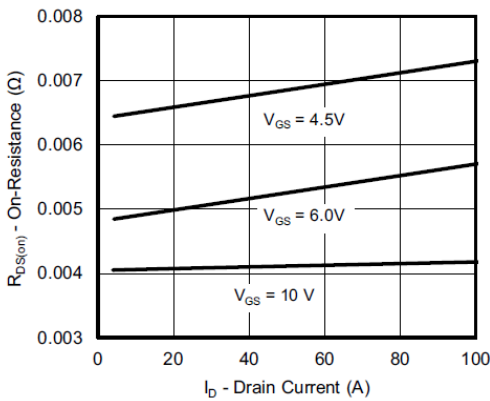
● Typical Performance Characteristics (T_J = 25 °C, unless otherwise noted)



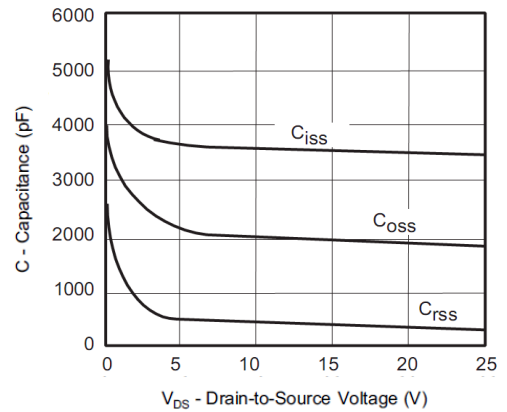
Output Characteristics



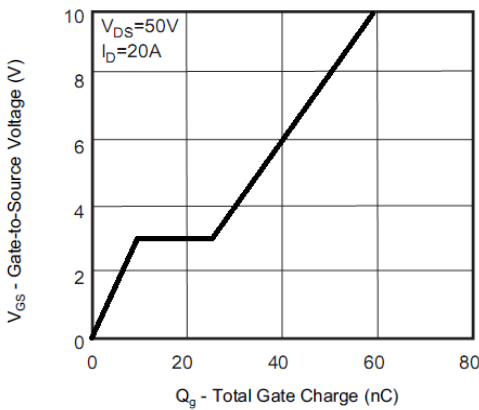
Transfer Characteristics



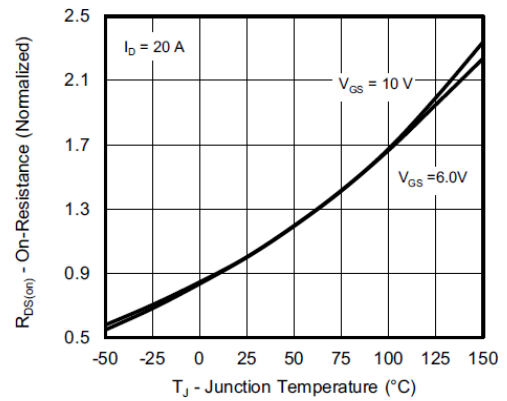
On-Resistance vs. Drain Current and Gate Voltage



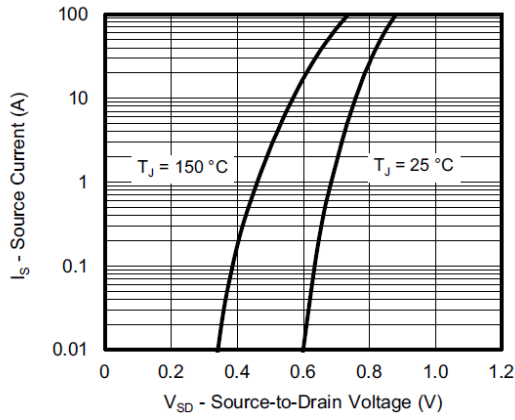
Capacitance



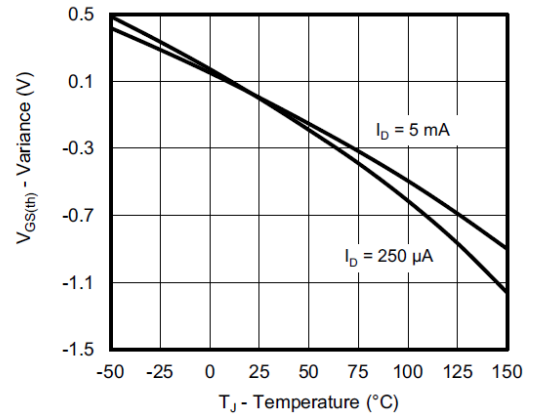
Gate Charge



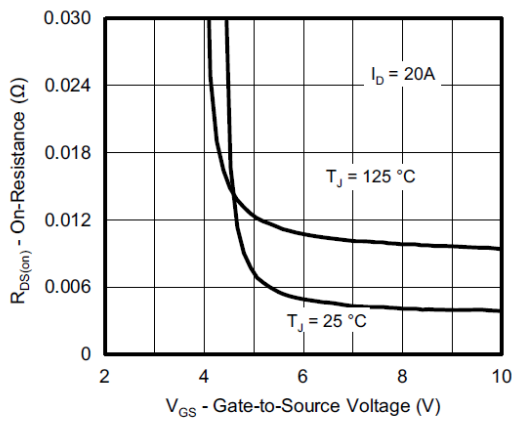
On-Resistance vs. Junction Temperature



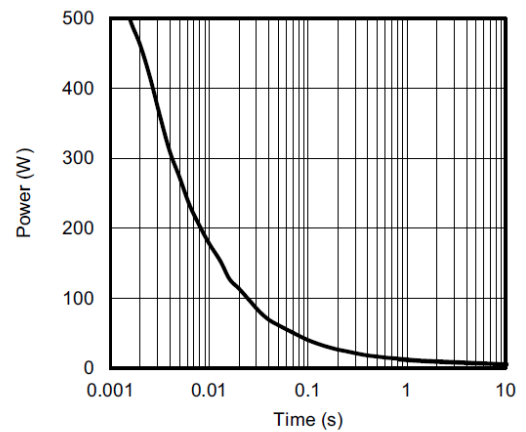
Source-Drain Diode Forward Voltage



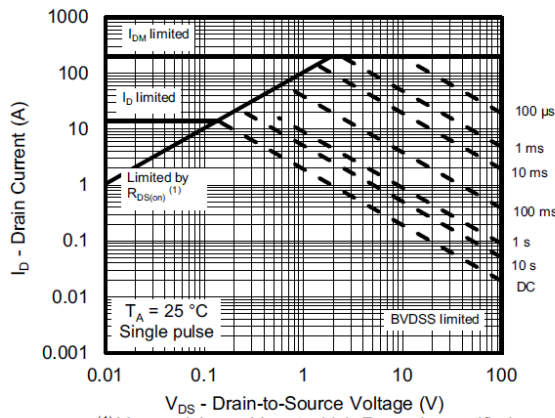
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

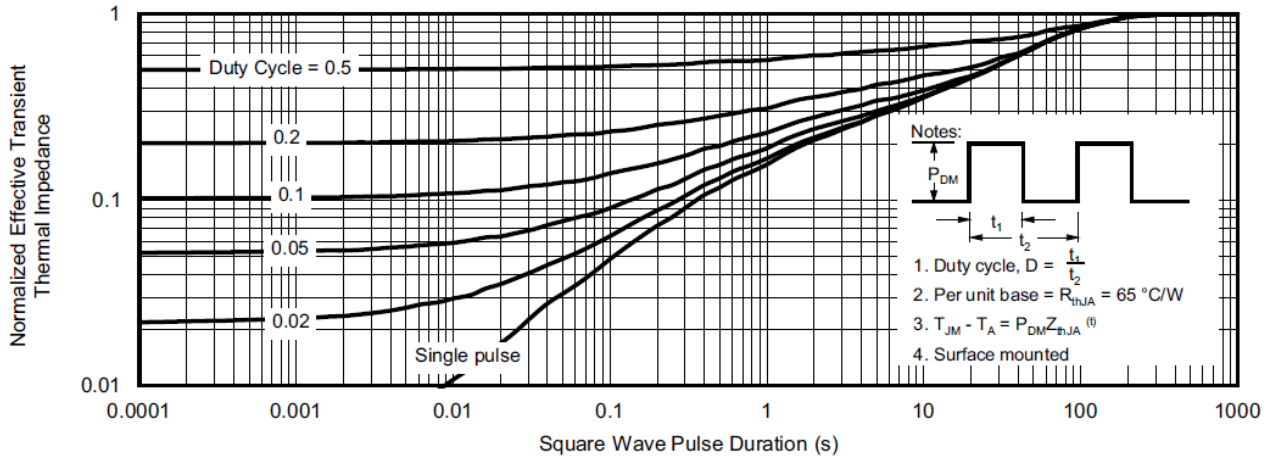


Single Pulse Power, Junction-to-Ambient

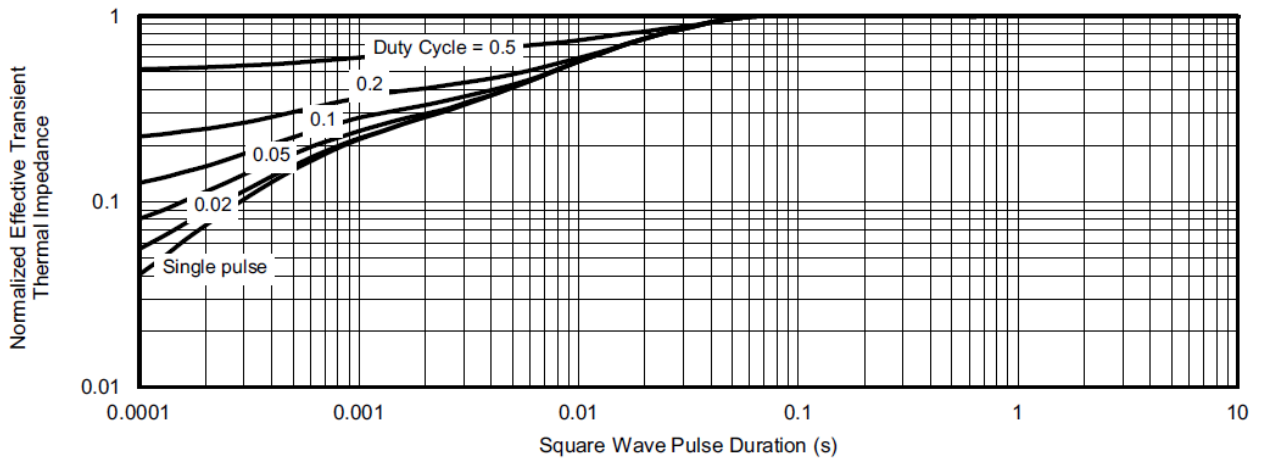


(1) $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

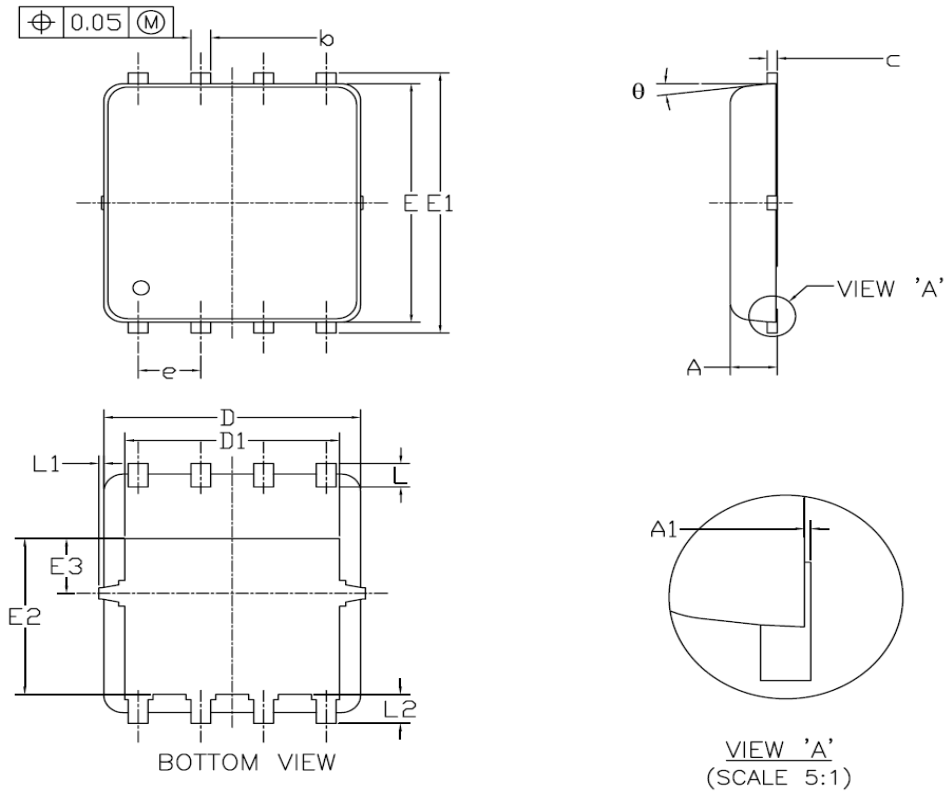
Safe Operating Area, Junction-to-Ambient



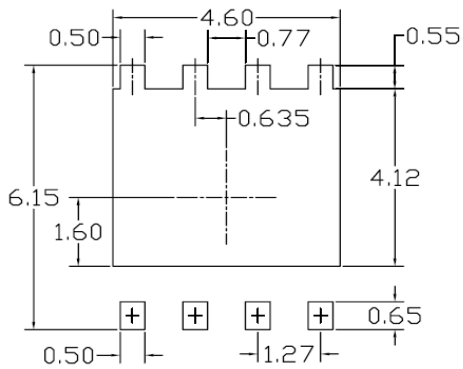
Normalized Thermal Transient Impedance, Junction-to-Ambient



● **Package Information**



RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.20 BSC			0.205 BSC		
D1	4.35 BSC			0.171 BSC		
E	5.55 BSC			0.219 BSC		
E1	6.05 BSC			0.238 BSC		
E2	3.625 BSC			0.143 BSC		
E3	1.275 BSC			0.050 BSC		
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
θ	0°	---	10°	0°	---	10°

UNIT: mm

NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.